

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
30V	20mΩ @ V _{GS} = 10V	7.7A
	32mΩ @ V _{GS} = 4.5V	6.1A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

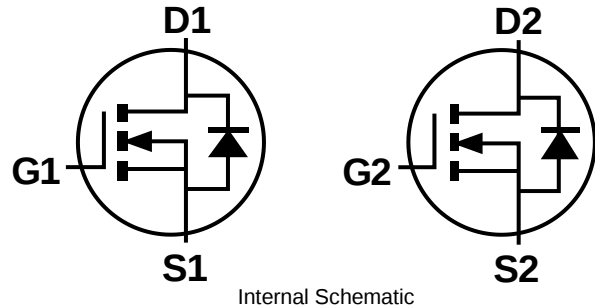
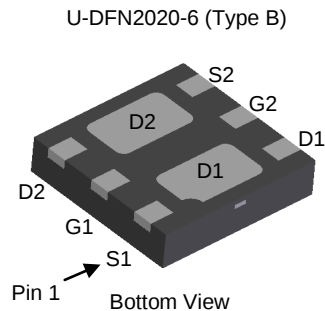
- General Purpose Interfacing Switch
- Power Management Functions

Features and Benefits

- 0.6mm Profile – Ideal for Low Profile Applications
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: U-DFN2020-6 (Type B)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ^(e4)
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

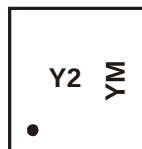


Ordering Information (Note 4)

Part Number	Case	Packaging
DMT3020LFDB-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMT3020LFDB-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



Y2 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: F = 2018)
M = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021
Code	C	D	E	F	G	H	I

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +75°C	I _D	7.7 6.2	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	2	A
Pulsed Drain Current (380μs Pulse, Duty Cycle = 1%)			I _{DM}	50	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P _D	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	170	°C/W
Total Power Dissipation (Note 6)		P _D	1.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	70	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	µA	V _{DS} = 24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	2.5	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	—	20	mΩ	V _{GS} = 10V, I _D = 9.0A
				32		V _{GS} = 4.5V, I _D = 7.0A
Diode Forward Voltage	V _{SD}	—	—	1.0	V	V _{GS} = 0V, I _S = 2A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	393	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	173	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	27	—	pF	
Gate Resistance	R _G	—	1.1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 10V)	Q _G	—	7.0	—	nC	V _{DD} = 15V, I _D = 9A
Total Gate Charge (V _{GS} = 4.5V)	Q _G	—	3.6	—	nC	
Gate-Source Charge	Q _{GS}	—	0.9	—	nC	
Gate-Drain Charge	Q _{GD}	—	1.5	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	1.8	—	ns	V _{DD} = 15V, V _{GS} = 10V, R _G = 6Ω, I _D = 9A
Turn-On Rise Time	t _R	—	1.9	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	7.5	—	ns	
Turn-Off Fall Time	t _F	—	2.4	—	ns	I _F = 9A, di/dt = 100A/µs
Reverse Recovery Time	t _{RR}	—	10	—	ns	
Reverse Recovery Charge	Q _{RR}	—	2.6	—	nC	

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.

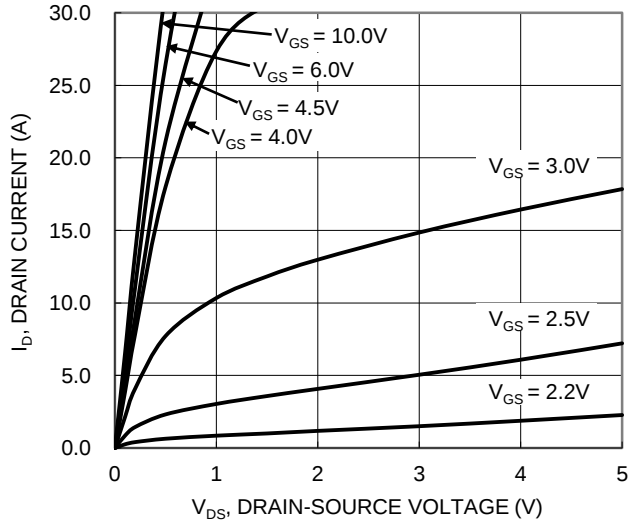


Figure 1. Typical Output Characteristic

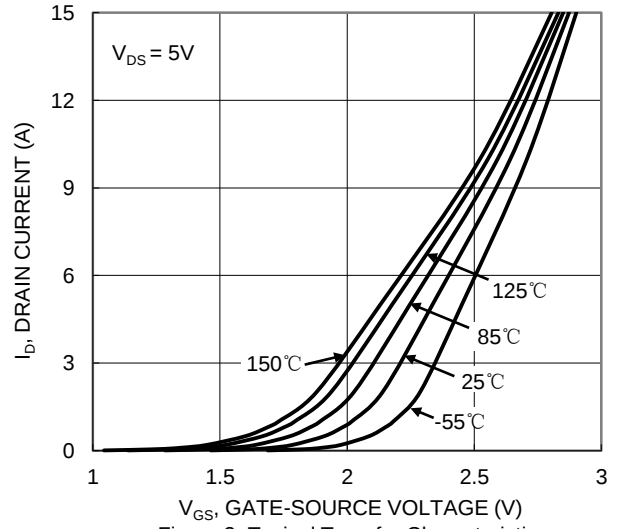


Figure 2. Typical Transfer Characteristic

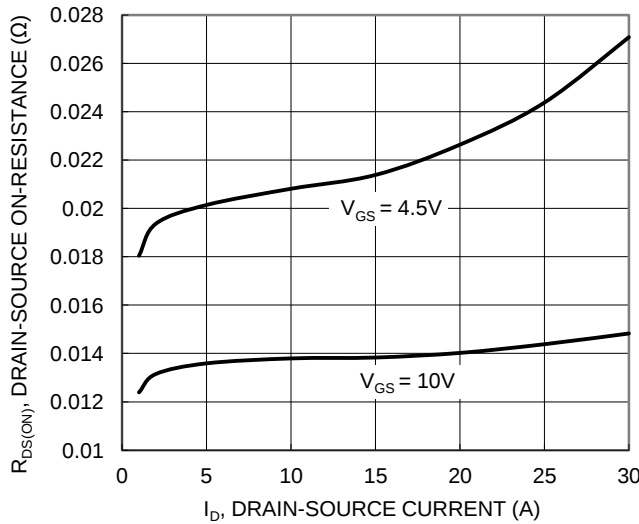


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

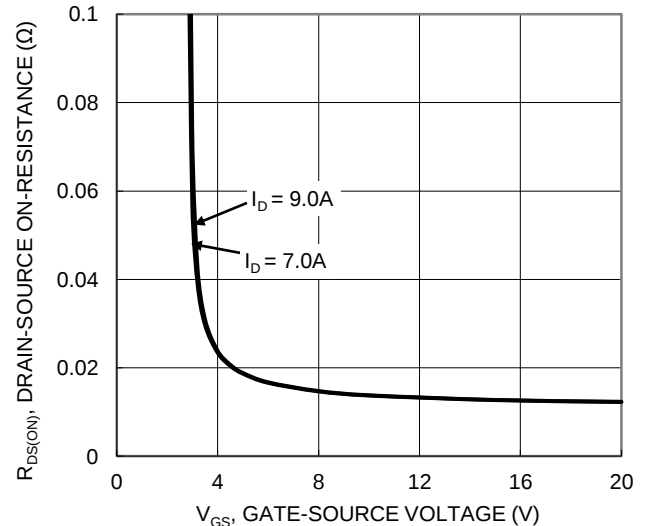


Figure 4. Typical Transfer Characteristic

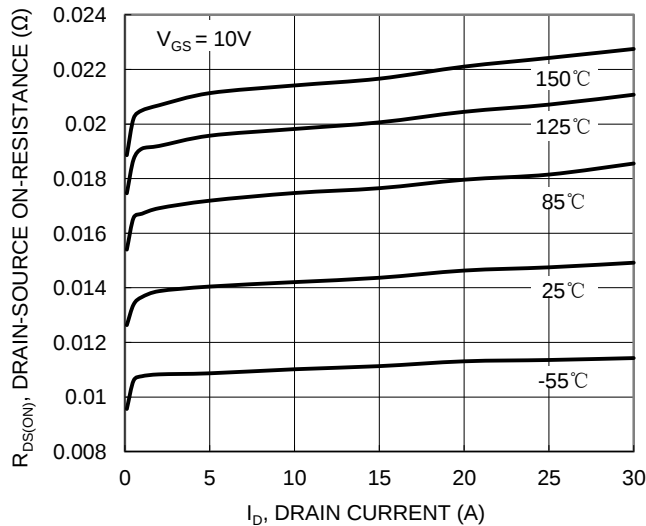


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

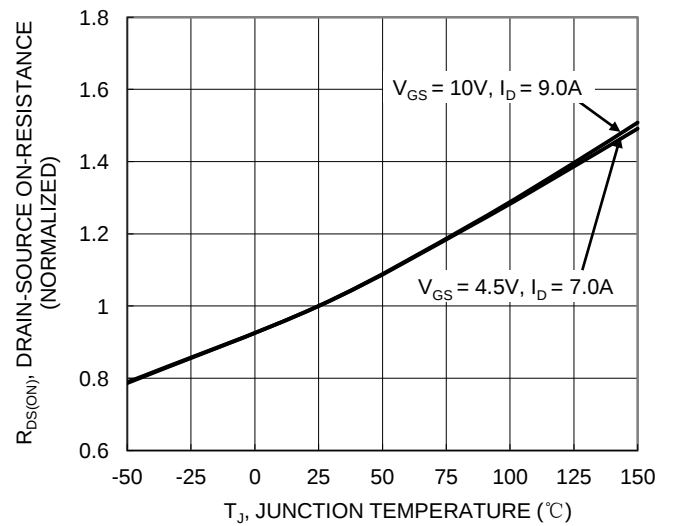
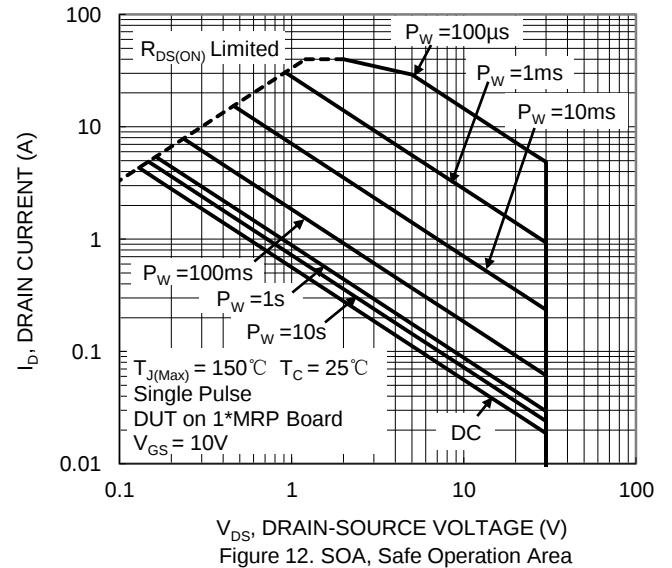
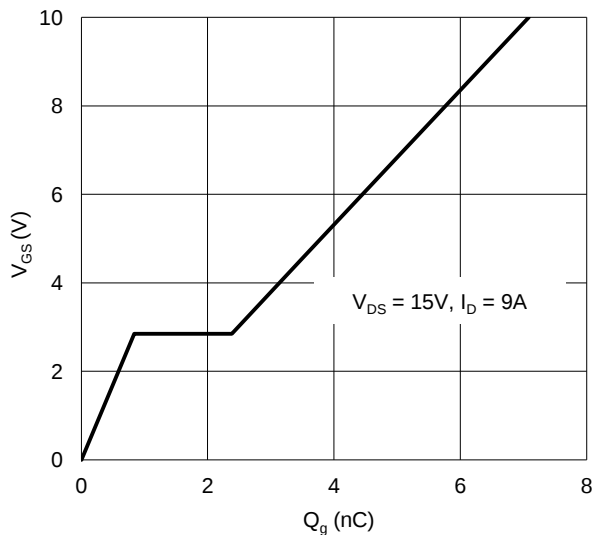
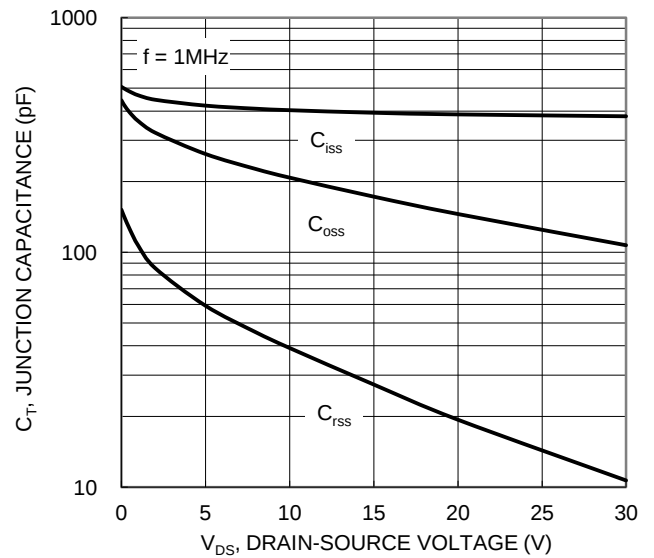
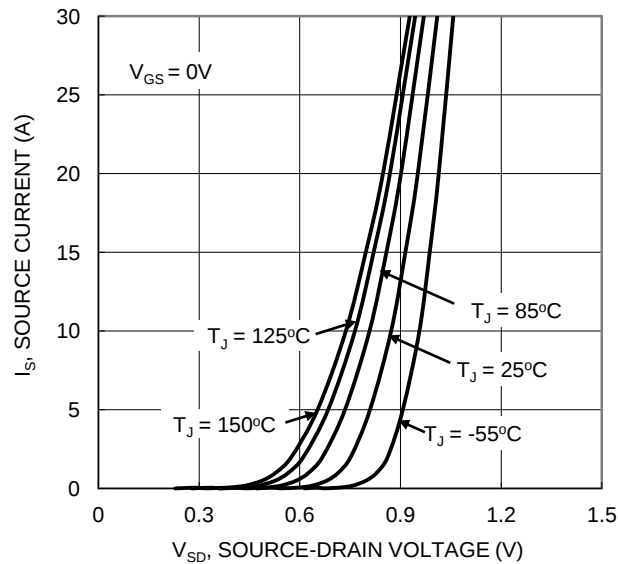
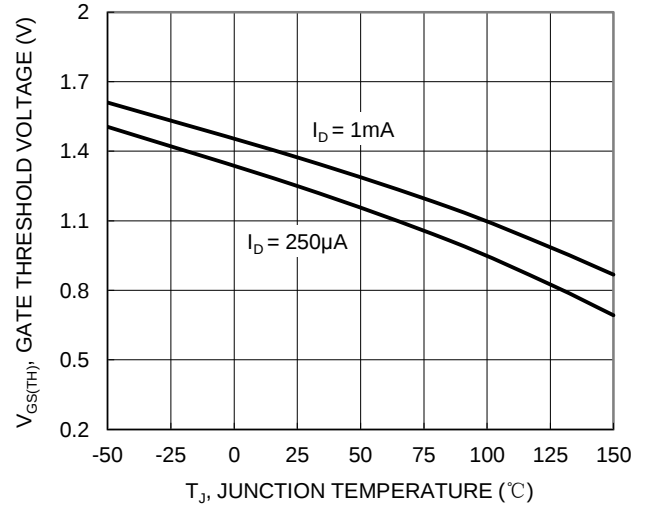
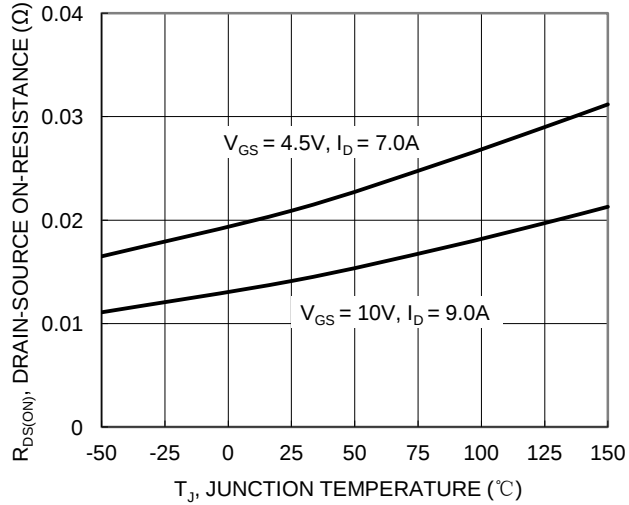


Figure 6. On-Resistance Variation with Junction Temperature



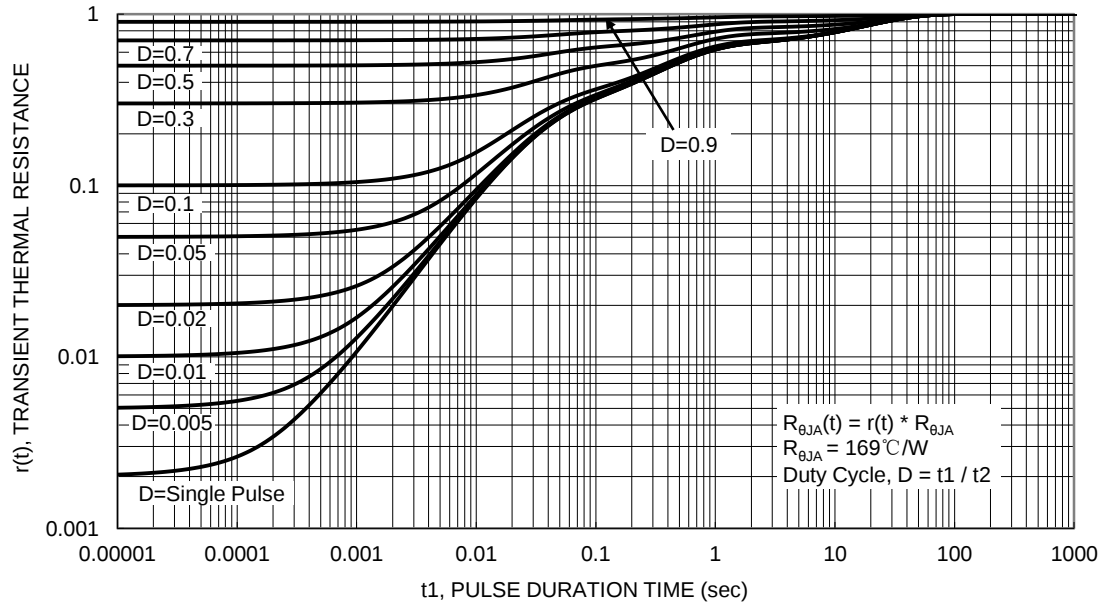
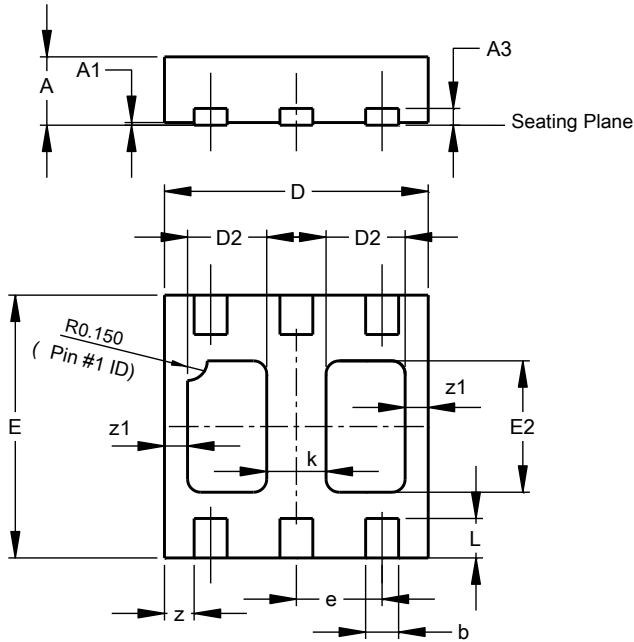


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type B)

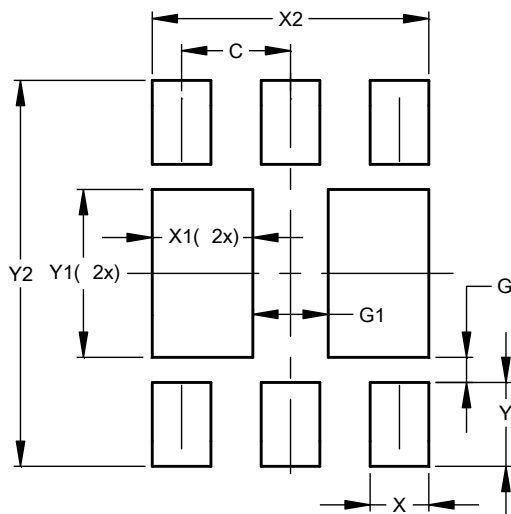


U-DFN2020-6 Type B			
Dim	Min	Max	Typ
A	0.545	0.605	0.575
A1	0.00	0.05	0.02
A3	-	-	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
D2	0.50	0.70	0.60
e	-	-	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
k	-	-	0.45
L	0.25	0.35	0.30
z	-	-	0.225
z1	-	-	0.175
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value (in mm)
C	0.650
G	0.150
G1	0.450
X	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300

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